Supporting Information

Enhancement of thermoelectric performance of SnTe via Mn solubility control

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Nominal composition	Density (g/cm ³)	Relative density (%)
Sn _{1.03} Te	6.276	97.2
Sn _{1.03} Te +3% AgBiSe ₂	6.393	99.0
$Sn_{0.93}Ge_{0.1}Te +3\% AgBiSe_2$	6.276	97.2
$Sn_{0.93}Mn_{0.1}Te +3\% AgBiSe_2$	6.225	96.4
$Sn_{0.83}Ge_{0.1}Mn_{0.1}Te + 3\% AgBiSe_2$	6.188	95.8
$Sn_{0.73}Ge_{0.1}Mn_{0.2}Te +3\% AgBiSe_2$	6.210	96.1

Table S1 Densities of $Sn_{1.03}$ Te and Ge, Mn and AgBiSe₂-alloyed $Sn_{1.03}$ Te.



Figure S1 Scanning electron microscopy (SEM) image and the corresponding energy-dispersive Xray spectroscopy (EDS) mapping of Sn_{0.93}Mn_{0.1}Te+3% AgBiSe₂.



Figure S2 The temperature-dependent (a) electrical resistivity, (b) Seebeck coefficient, and (c) power factor of $Sn_{0.73}Ge_{0.1}Mn_{0.2}Te +3\%$ AgBiSe₂ during a heating-cooling cycle.